2-input OR gate Rev. 05 — 14 March 2008

## 1. General description

74HC1G32 and 74HCT1G32 are high-speed Si-gate CMOS devices. They provide a 2-input OR function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC32 and 74HCT32.

### 2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options

## 3. Ordering information

### Table 1. Ordering information

Type number	Package						
	Temperature range	Name	Description	Version			
74HC1G32GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads;	SOT353-1			
74HCT1G32GW			body width 1.25 mm				
74HC1G32GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753			
74HCT1G32GV							

### 4. Marking

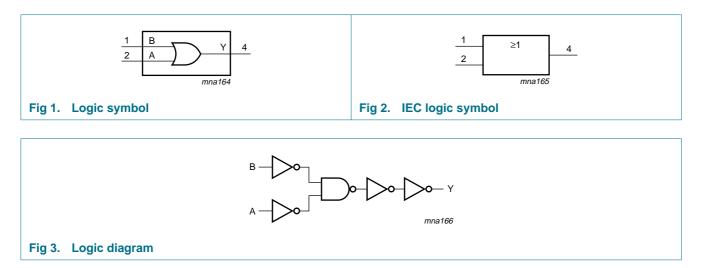
#### Table 2. Marking codes

Type number	Marking code
74HC1G32GW	HG
74HCT1G32GW	TG
74HC1G32GV	H32
74HCT1G32GV	T32



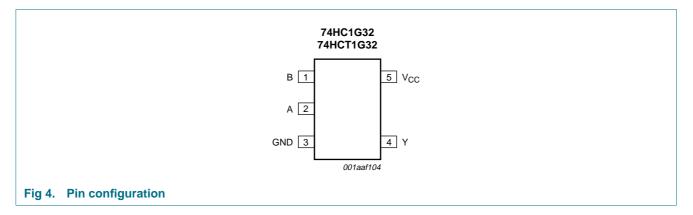
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## 5. Functional diagram



## 6. Pinning information

## 6.1 Pinning



### 6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
В	1	data input B
А	2	data input A
GND	3	ground (0 V)
Y	4	data output Y
V <sub>CC</sub>	5	supply voltage

## 7. Functional description

### Table 4.Function table

*H* = *HIGH* voltage level; *L* = *LOW* voltage level

Inputs		Output
Α	В	Y
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_{\rm I}$ < -0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
I <sub>OK</sub>	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I <sub>CC</sub>	supply current		-	25	mA
I <sub>GND</sub>	ground current		-25	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \text{ to } +125 \ ^{\circ}C$	[2] _	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C the value of  $\mathsf{P}_{tot}$  derates linearly with 2.5 mW/K.

## 9. Recommended operating conditions

#### Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol Parameter		Conditions	74HC10		2	74HCT1G32			Unit
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
é	and fall rate	$V_{CC} = 4.5 V$	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

2-input OR gate

# **10. Static characteristics**

### Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb} = 25 \degree C$ .

Symbol	Parameter	Conditions	-40	°C to +8	35 °C	–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	
74HC1G3	32							
V <sub>IH</sub> HIGH-level input voltage		$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	V
		$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	V
VIL	LOW-level input	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	V
	voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_{O} = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 4.5 \ V$	4.4	4.5	-	4.4	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	V
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
		$I_{O} = -2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V
V <sub>OL</sub>	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_0 = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	V
		$I_0 = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
		$I_0 = 2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	1.0	-	1.0	μA
I <sub>CC</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 6.0 \ V \end{array}$	-	-	10	-	20	μA
Cı	input capacitance		-	1.5	-	-	-	pF
74HCT1G	32							
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
VIL	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V <sub>он</sub>	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$						
	voltage	$I_{O} = -20 \ \mu A$	4.4	4.5	-	4.4	-	V
		$I_{O} = -2.0 \text{ mA}$	4.13	4.32	-	3.7	-	V
V <sub>OL</sub>	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$						
	voltage	I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 2.0 mA	-	0.15	0.33	-	0.4	V
lı	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	1.0	-	1.0	μΑ

2-input OR gate

Voltages a	re referenced to GND (g	round = 0 V). All typical values are	measur	ed at T <sub>a</sub>	<sub>mb</sub> = 25	° <i>C</i> .		
Symbol	Parameter	Conditions	–40 °C to +85 °C			_40 °C t	Unit	
			Min	Тур	Max	Min	Max	
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	10	-	20	μΑ
$\Delta I_{CC}$	additional supply current	per input; V <sub>CC</sub> = 4.5 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; I <sub>O</sub> = 0 A	-	-	500	-	850	μΑ
CI	input capacitance		-	1.5	-	-	-	pF

#### Table 7. Static characteristics ... continued

## **11. Dynamic characteristics**

#### Table 8. Dynamic characteristics

GND = 0 V;  $t_r = t_f \le 6.0$  ns. All typical values are measured at  $T_{amb} = 25 \circ C$ . For test circuit see Figure 6

Symbol	Parameter	Conditions		<b>−40 °C to +85 °C</b>			<b>−40</b> °C t	Unit	
			-	Min	Тур	Max	Min	Max	
74HC1G	32	'							
t <sub>pd</sub>	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	18	115	-	135	ns
		$V_{CC} = 4.5 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	8	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	8	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	7	20	-	23	ns
C <sub>PD</sub>	power dissipation capacitance	$V_I = GND$ to $V_{CC}$	[2]	-	19	-	-	-	pF
74HCT1	G32								
t <sub>pd</sub>	propagation delay	A and B to Y; see Figure 5	[1]						
		$V_{CC} = 4.5 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	10	24	-	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	10	-	-	-	ns
C <sub>PD</sub>	power dissipation capacitance	$V_I = GND$ to $V_{CC} - 1.5$ V	[2]	-	20	-	-	-	pF

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[2]  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D$  ( $\mu$ W).

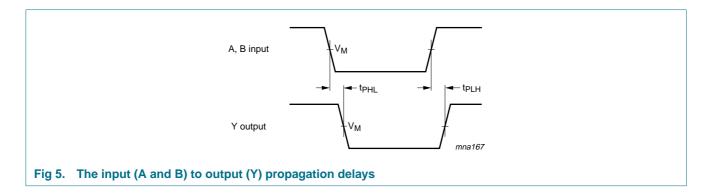
$$\begin{split} P_D &= C_{PD} \times V_{CC}^2 \times f_i + \sum \left( C_L \times V_{CC}^2 \times f_o \right) \text{ where:} \\ f_i &= \text{input frequency in MHz} \\ f_o &= \text{output frequency in MHz} \\ C_L &= \text{output load capacitance in pF} \end{split}$$

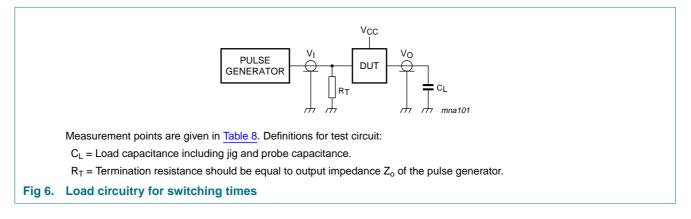
 $V_{CC}$  = supply voltage in V

 $\Sigma~(C_L \times V_{CC}{}^2 \times f_o)$  = sum of outputs

2-input OR gate

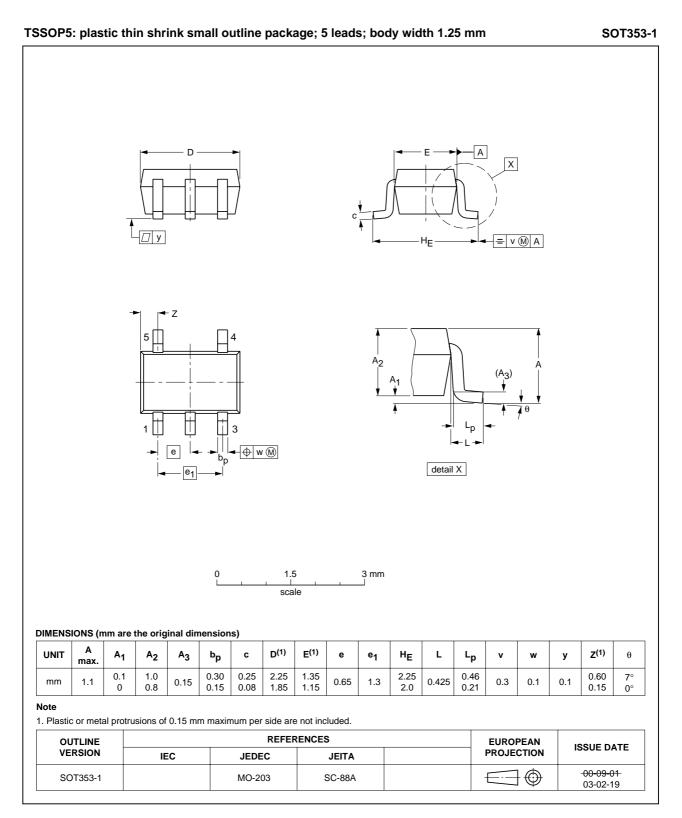
# 12. Waveforms





2-input OR gate

## 13. Package outline



### Fig 7. Package outline SOT353-1 (TSSOP5)

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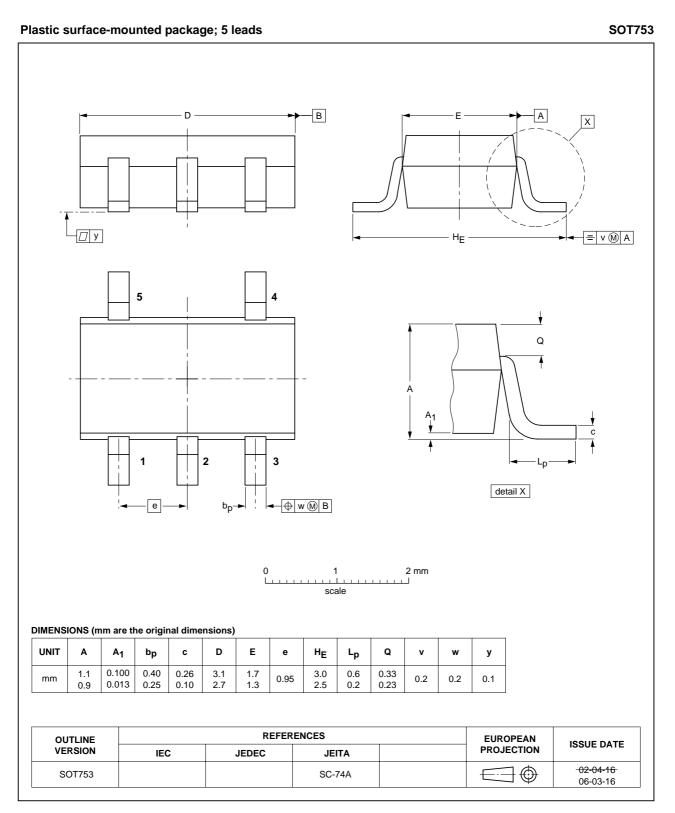


Fig 8. Package outline SOT753 (SC-74A)

2-input OR gate

# 14. Abbreviations

Table 9.	Abbreviations		
Acronym	Description		
DUT	Device Under Test		
TTL	Transistor-Transistor Logic		

# 15. Revision history

#### Table 10.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G32_5	20080314	Product data sheet	-	74HC_HCT1G32_4
Modifications:	<ul> <li>Pin descript</li> </ul>	tion of Pin 4 changed from inp	ut to output in Table 3	<u>3</u> .
74HC_HCT1G32_4	20070514	Product data sheet	-	74HC_HCT1G32_3
74HC_HCT1G32_3	20020515	Product specification	-	74HC_HCT1G32_2
74HC_HCT1G32_2	20010406	Product specification	-	74HC_HCT1G32
74HC_HCT1G32	19971216	Preliminary specification	-	-

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### 16.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
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### **18. Contents**

1	General description 1
2	Features 1
3	Ordering information 1
4	Marking 1
5	Functional diagram 2
6	Pinning information 2
6.1 6.2	Pinning
0. <u>2</u> 7	Functional description
8	Limiting values
9	Recommended operating conditions
10	Static characteristics
11	Dynamic characteristics 5
12	Waveforms
13	Package outline 7
14	Abbreviations
15	Revision history9
16	Legal information 10
16.1	Data sheet status 10
16.2	Definitions 10
16.3	Disclaimers
16.4	Trademarks 10
17	Contact information 10
18	Contents 11

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